Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-540-9621
Inclosure Material:
Metal
Overall Length:
1.550 inches
Overall Height:
0.300 inches
Overall Width:
1.050 inches
Function For Which Designed:
Amplifier
Mounting Facility Quantity:
2
Component Name And Quantity:
2 transistor
Mounting Method:
Unthreaded hole
Features Provided:
Burn in
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
60.0 breakdown voltage, collector-to-base, emitter open all transistor and 60.0 breakdown voltage, collector-to-emitter, base open all
transistor and 5.0 breakdown voltage, emitter-to-base, collector open all transistor
Current Rating Per Characteristic:
0.20 amperes source cutoff current all transistor and 10.00 amperes source cutoff current all transistor
Power Rating Per Characteristic:
150.0 watts small-signal input power, common-collector absolute all transistor
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius ambient air
Special Features:
Internal junction configuration transistor pnp
Terminal Type And Quantity:
1 case and 2 pin
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Filg:
A110a0